RGTH40TS65DGC13

650V 20A Field Stop Trench IGBT

Datasheet

V _{CES}	650V
I _{C(100°C)}	20A
V _{CE(sat) (Typ.)}	1.6V
P_D	144W

● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD (RFN Series)
- 5) Pb free Lead Plating; RoHS Compliant

Applications

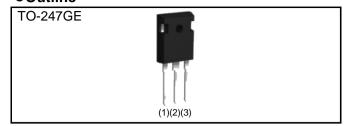
PFC

UPS

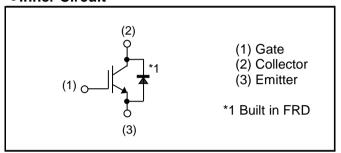
Power Conditioner

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	600
	Packing code	C13
	Marking	RGTH40TS65D

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	40	А
Collector Current	$T_C = 100$ °C	I _C	20	А
Pulsed Collector Current		I _{CP} *1	80	А
Diode Forward Current	T _C = 25°C	I _F	35	А
	$T_C = 100$ °C	l _F	20	А
Diode Pulsed Forward Current		I _{FP} *1	80	А
Dower Dissipation	$T_C = 25^{\circ}C$	P _D	144	W
Power Dissipation	$T_C = 100$ °C	P _D	72	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Linit
Farameter		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.04	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.28	°C/W

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_C = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	ı	-	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	•	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 13.3 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 20A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1	V

ullet **IGBT Electrical Characteristics** (at $T_j = 25$ °C unless otherwise specified)

Doromotor	Symbol	Conditions	Values			Unit
Parameter			Min.	Тур.	Max.	Offic
Input Capacitance	C_{ies}	V _{CE} = 30V	-	1060	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	47	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	18	-	
Total Gate Charge	Q _g	V _{CE} = 300V	-	40	-	
Gate - Emitter Charge	Q_ge	I _C = 20A	-	9	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	15	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 20A, V_{CC} = 400V$	-	22	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	25	-	200
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	73	-	ns
Fall Time	t _f	Inductive Load	-	48	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 20A, V_{CC} = 400V$	-	22	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	25	-	no
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	83	-	ns
Fall Time	t _f	Inductive Load	-	58	-	
		$I_C = 80A, V_{CC} = 520V$				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Datasheet

•FRD Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			l lm:t
			Min.	Тур.	Max.	Unit
Diode Forward Voltage	V _F	$I_F = 20A$ $T_j = 25$ °C $T_j = 175$ °C	-	1.45 1.25	1.9 -	V
Diode Reverse Recovery Time	t _{rr}	I _F = 20A	-	58	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	V _{CC} = 400V di _F /dt = 200A/μs	-	6.3	-	А
Diode Reverse Recovery Charge	Q_{rr}	T _j = 25°C	-	0.20	-	μC
Diode Reverse Recovery Time	t _{rr}	I _F = 20A	-	256	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	V _{CC} = 400V di _F /dt = 200A/μs	-	10.4	-	А
Diode Reverse Recovery Charge	Q _{rr}	T _j = 175°C	-	1.35	-	μC

Fig.1 Power Dissipation vs. Case Temperature

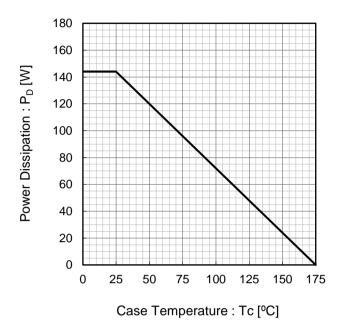
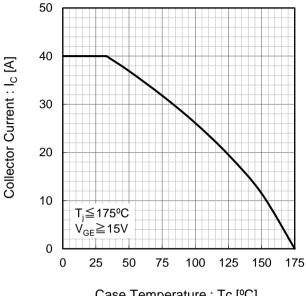


Fig.2 Collector Current vs. Case Temperature



Case Temperature : Tc [°C]

Fig.3 Forward Bias Safe Operating Area

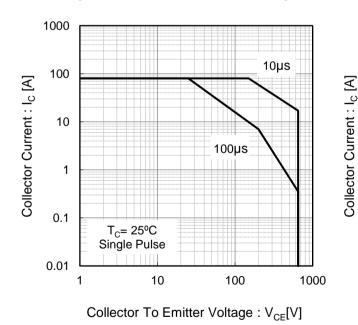
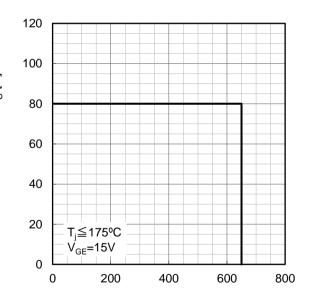


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.5 Typical Output Characteristics

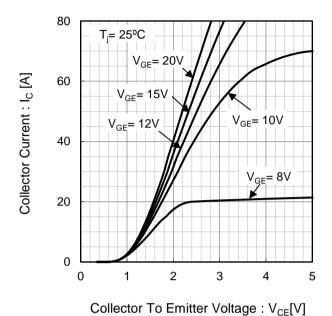
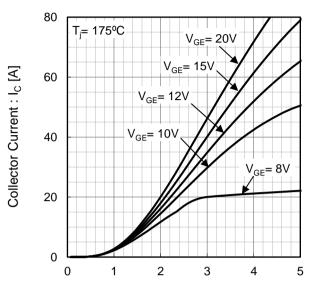


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.7 Typical Transfer Characteristics

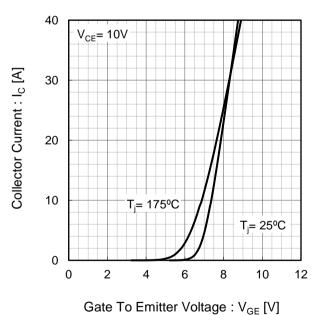
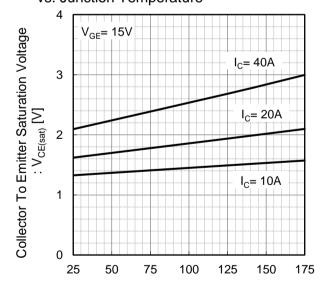
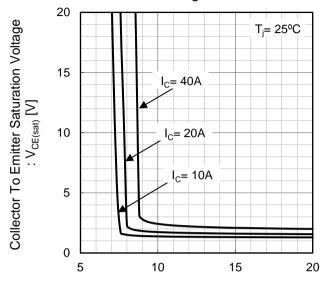


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



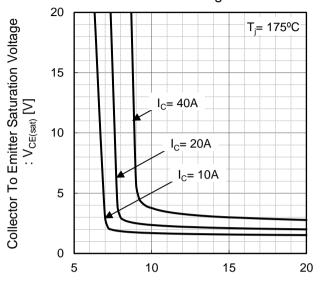
Junction Temperature : T_i [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



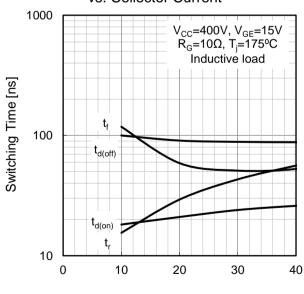
Gate To Emitter Voltage : V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



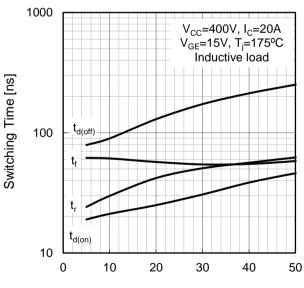
Gate To Emitter Voltage: V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current



Collector Current : I_C [A]

Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance : $R_G[\Omega]$

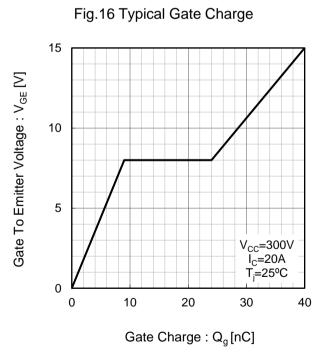
Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ E_{on} 0.1 V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175°C Inductive load 0.01 0 10 20 30 40 Collector Current : I_C [A]

vs. Gate Resistance 10 1 $\mathsf{E}_{\mathsf{off}}$ E_{on} 0.1 V_{CC}=400V, I_C=20A V_{GE}=15V, T_j=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Switching Energy Losses [mJ]

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] 100 Coes Cres 10 f=1MHz $V_{GE}=0V$ T_i=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : $V_{CE}[V]$



Forward Current: I_F [A]

40

20

0

0

0.5

•Electrical Characteristic Curves

vs. Forward Voltage

80

60

Fig.17 Typical Diode Forward Current

Forward Voltage: V_F[V]

1.5

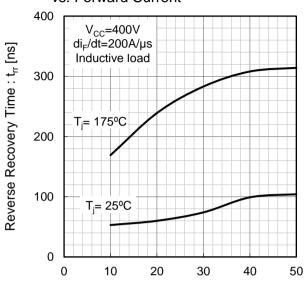
T_i= 25°C

2

2.5

3

Fig.18 Typical Diode Reverse Recovery Time vs. Forward Current



Forward Current : I_F [A]

Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

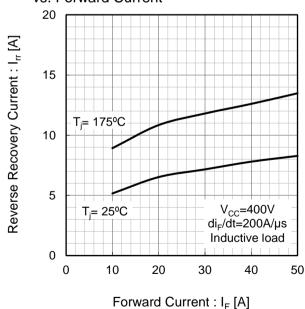
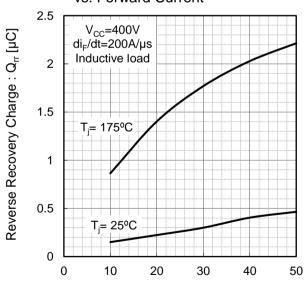


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



Forward Current : I_F [A]

Fig.21 IGBT Transient Thermal Impedance

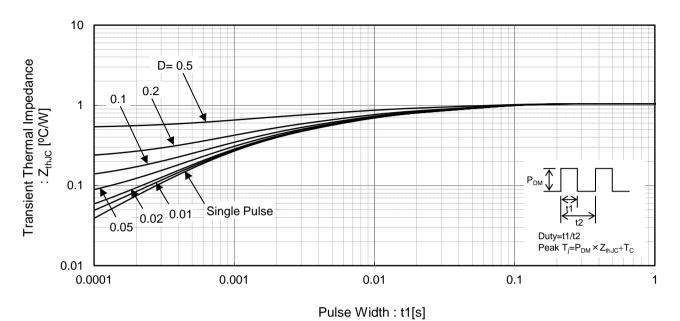
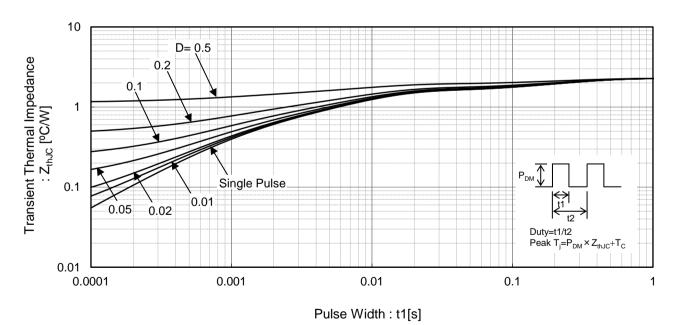


Fig.22 Diode Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

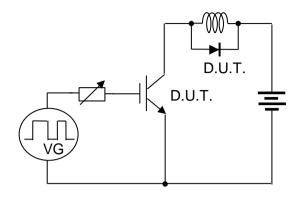


Fig.23 Inductive Load Circuit

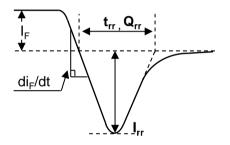


Fig.25 Diode Reverce Recovery Waveform

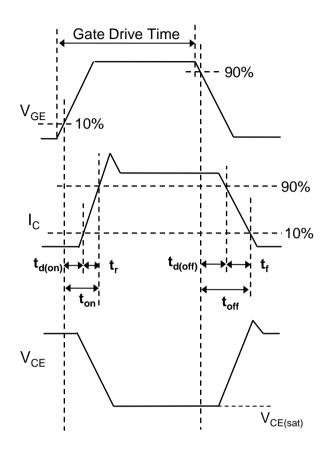


Fig.24 Inductive Load Waveform

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